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 TI Copper alloy sputtering target and
 manufacture of semiconductor device using it
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AB The Cu-base sputtering target contains 0.02-20 atomic% Al and/or Si. The manufacture of the semiconductor device involves (1) sputtering with the target to form a thin-film wiring on a substrate and (2) forming an oxide film on the wiring surface. The wiring in the device showed good electromigration and stress-migration resistances.